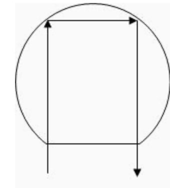
Icemos Technology Ltd **Product Specification** **1003.009501** Issue Date 16 September 2014 22

Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	None	
	5.0	Overall Thickness	404.00 +/- 16.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00um	ADE, 100% measurement
	7.0	Bow	<30.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<30.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
	11.0	Growth Method	CZ	Wafer Vendor
	12.0	Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Type	Any	Wafer Vendor
DeviceSilicon	14.0	Device Dopant	Any	Wafer Vendor
OverallWafer	15.0	Resistivity	1 - 25 Ohmcm	Wafer Vendor
	16.0	Frontsurface condition	Frontside - polished with oxide.	Wafer Vendor
	17.0	Backsurface condition	Backside - polished with oxide.	Implant vendor
	18.0	Frontside final oxide thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	19.0	Back side Oxide Thickness	20000A	Not measured
HandleSilicon	20.0	Handle Thickness	400.00 +/- 15.00 um	ADE, 100%
	21.0	Total scratch length	<25mm Total	Bright Light, 100% (note 2)
	22.0	Surface Haze	none	Bright Light, 100% (note 2)

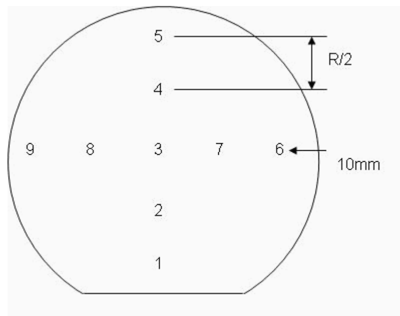
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information